Notification about the transfer of the semiconductor business

The semiconductor business of Panasonic Corporation will be transferred on September 1, 2020 to Nuvoton Technology Corporation (hereinafter referred to as "Nuvoton"). Accordingly, Panasonic Semiconductor Solutions Co., Ltd. will come under the umbrella of the Nuvoton Group, with the new name of Nuvoton Technology Corporation Japan (hereinafter referred to as "NTCJ").

In accordance with this transfer, semiconductor products will be handled as NTCJ-made products after September 1, 2020. However, such products will be continuously sold through Panasonic Corporation.

Publisher of this Document is NTCJ.

If you would find description "Panasonic" or "Panasonic semiconductor solutions", please replace it with NTCJ.

Except below description page
 "Request for your special attention and precautions in using the technical information and semiconductors described in this book"

Nuvoton Technology Corporation Japan

ADVANCE INFORMATION

Product Standards

MOS FET

FJ4B0334ZL

Panasonic

FJ4B0334ZL

All in one P-channel MOS FET

■ Features

- · For passive cell balancing circuits
- Built-in cell discharge resistor, gate-source resistor and zener diode
- CSP(Chip Size Package)
- Halogen-free / RoHS compliant (EU RoHS / UL-94 V-0 / MSL : Level 1)

■ Marking Symbol: 2H

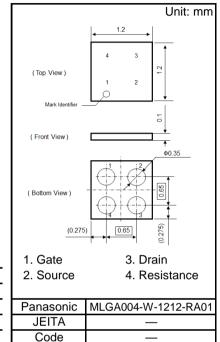
■ Packaging

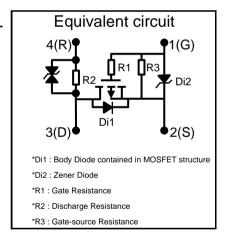
Embossed type (Thermo-compression sealing): 20 000 pcs / reel (standard)

■ Absolute Maximum Ratings Ta = 25 °C

Parameter	Symbol	Rating	Unit	
Drain-source Voltage	VDS	-30	V	
Gate-source Voltage	VGS	+0.5 / -5	V	
Source-resistance Current	DC	ISR *1	150	mA
Total Power Dissipation	PD *1	1.3	W	
Operating Junction and Storage Temperature Range		Tj,Tstg	-55 to +150	°C

Note *1 Mounted on FR4 board (25.4 mm x 25.4 mm x t1.0 mm).
FR4 board fully covered with copper pad (611 mm² area, 35 μm thickness).





Panasonic

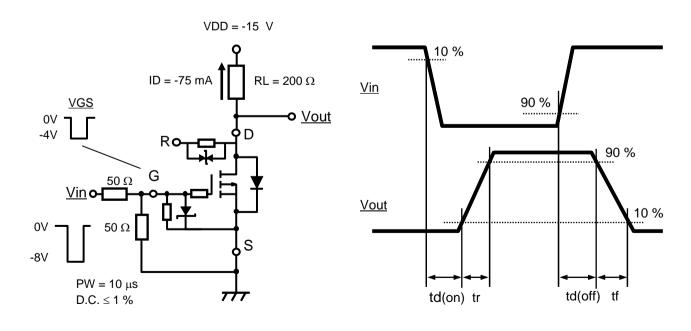
FJ4B0334ZL

■ Electrical Characteristics Ta = 25 °C ± 3 °C

Parameter	Symbol	Conditions		Тур	Max	Unit
Drain-source Breakdown Voltage	VDSS	IDS = -1 mA, VGS = 0 V	-30			V
Zero Gate Voltage Drain Current	IDSS	VDS = -30 V, VGS = 0 V			-1	μA
Gate-source Leakage Current	IGSS	VGS = -5 V, VDS = 0 V			-50	μA
Gate-source Threshold Voltage	Vth	IDS = -2.12 mA, VDS = -10 V	-0.3	-0.65	-1.05	V
Drain-source On-state Resistance	RDS(on)1	IDS = -75 mA, VGS = -4.5 V		100	350	mΩ
	RDS(on)2	IDS = -75 mA, VGS = -2.5 V		110	400	
	RDS(on)3	IDS = -75 mA, VGS = -1.5 V		140	1500	
Di1 Body Diode Forward Voltage	VF(s-d)	IF = -75 mA, VGS = 0 V		-0.60	-1.2	V
Di2 Zener Diode Forward Voltage	VF	IF = 100 μA		0.55	0.8	V
Zener Diode Reverse Voltage	VZ	IZ = -1 mA	-5.0	-7.5		V
Input Capacitance *1	Ciss	VDS = -15 V, VGS = 0 V		895		pF
Output Capacitance *1	Coss	f = 1 kHz		60		
Reverse Transfer Capacitance *1	Crss	I = I KIIZ		50		
Turn-on Delay Time *1,*2	td(on)	VDD = -15 V, VGS = 0 to -4 V		280		ns
Rise Time *1,*2	tr	IDS = -75 mA		400		
Turn-off Delay Time *1,*2	td(off)	VDD = -15 V, VGS = 0 to -4 V		2000		
Fall Time *1,*2	tf	IDS = -75 mA		1030		
Total Gate Charge *1	Qg1	VDD = -15 V, VGS = -1.5 V		3.9		nC
		IDS = -150 mA				
	Qg2	VDD = -15 V, VGS = -4 V		10.3		
Gate-source Charge *1	Qgs	IDS = -150 mA		0.9		
Gate-drain Charge *1	Qgd	1D3 = -130 IIIA		1.5		
R1 Gate Resistance *1	Rg	f = 1 MHz		1.0		kΩ
R2 Discharge Resistance	Rd	VRD = -1 V	45	50	55	Ω
R3 Gate-source Resistance*1	Rgs	VGS = -1 V	200	300	400	kΩ

Note Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.

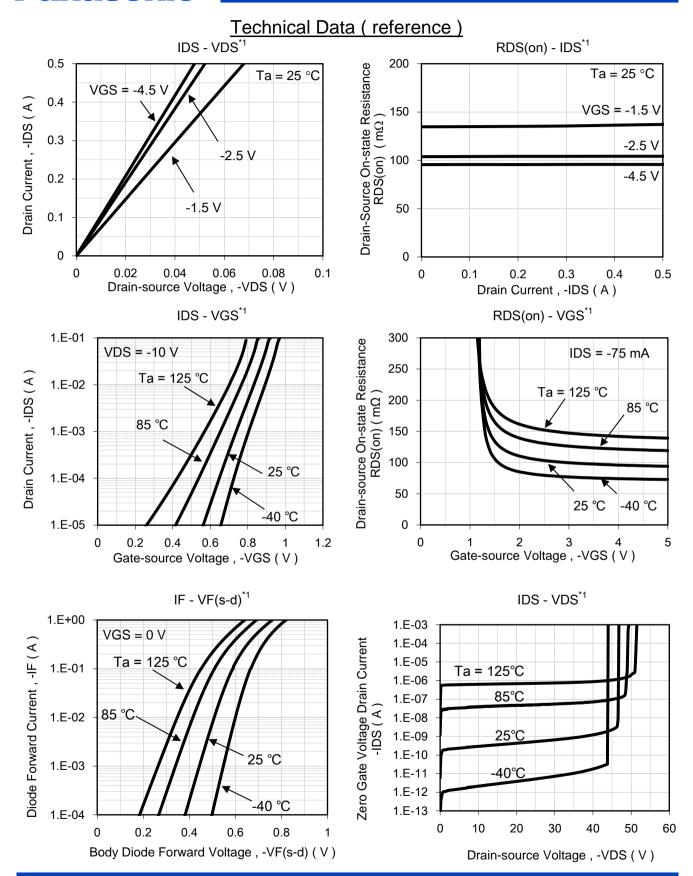
- *1 Guaranteed by design, not subject to production testing.
- *2 Measurement circuit for Turn-on Delay Time / Rise Time / Turn-off Delay Time / Fall Time.



MOS FET

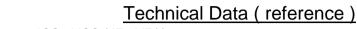
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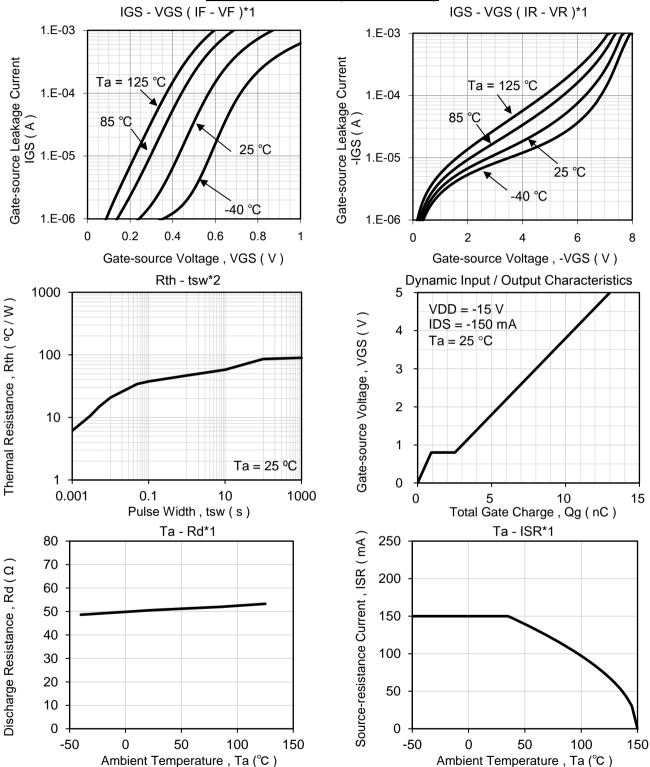
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MOS FET

Panasonic FJ4B0334ZL





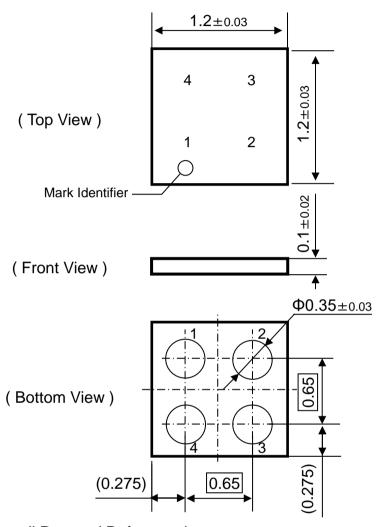
^{*1} Pulse measurement

^{*2} Mounted on FR4 board (25.4 mm × 25.4 mm × t1.0 mm). FR4 board fully covered with copper pad (611 mm² area, 35 μm thickness).

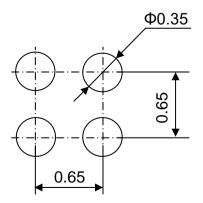
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Panasonic

■ Outline Unit: mm



■ Land & Stencil Pattern (Reference)



Unit: mm

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